

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1225

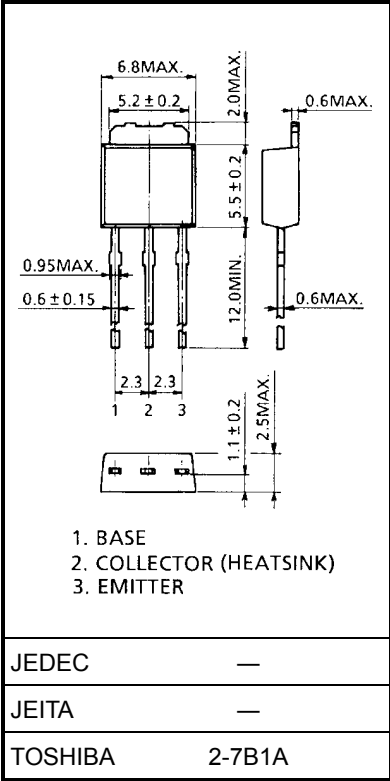
Power Amplifier Applications
Driver Stage Amplifier Applications

- High transition frequency: $f_T = 100\text{ MHz (typ.)}$
- Complementary to 2SC2983

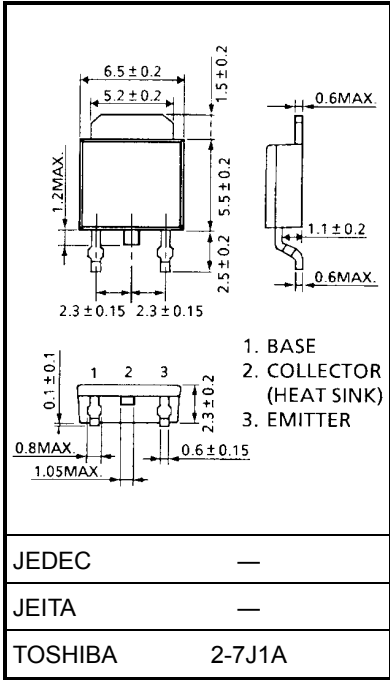
Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	-160	V
Collector-emitter voltage		V_{CEO}	-160	V
Emitter-base voltage		V_{EBO}	-5	V
Collector current		I_C	-1.5	A
Base current		I_B	-0.3	A
Collector power dissipation	Ta = 25°C	P_C	1.0	W
	Tc = 25°C		15	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Unit: mm



Weight: 0.36 g (typ.)



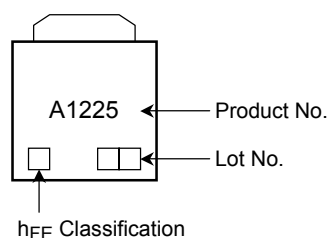
Weight: 0.36 g (typ.)

Electrical Characteristics (Ta = 25°C)

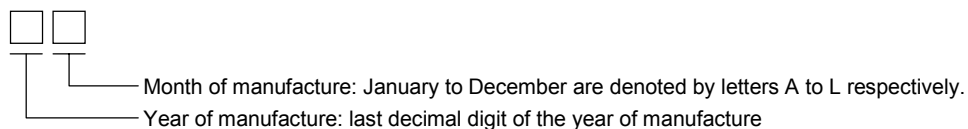
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -160\text{ V}, I_E = 0$	—	—	-1.0	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-160	—	—	V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{ mA}, I_C = 0$	-5	—	—	V
DC current gain	h_{FE} (Note)	$V_{CE} = -5\text{ V}, I_C = -100\text{ mA}$	70	—	240	
Collector emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$	—	—	-1.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$	—	—	-1.0	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -100\text{ mA}$	—	100	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	30	—	pF

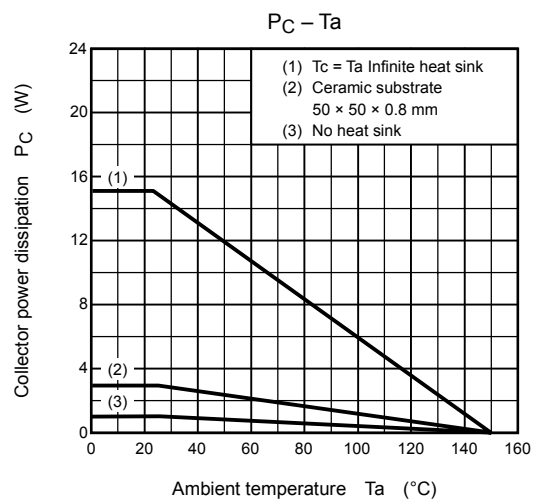
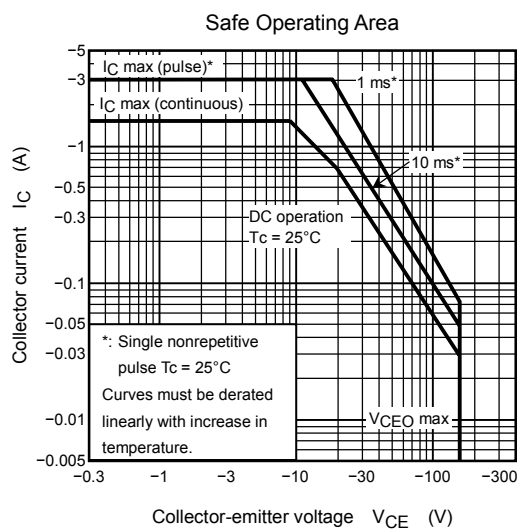
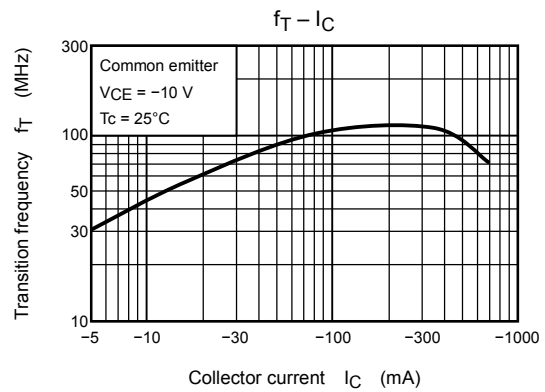
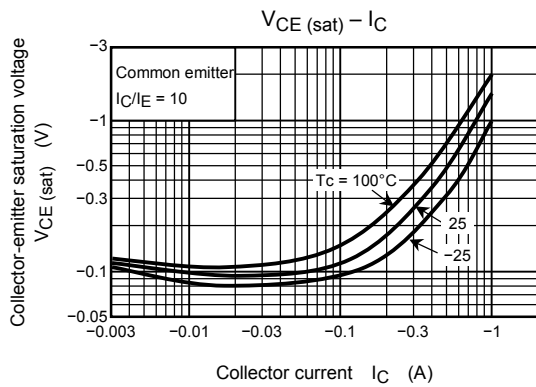
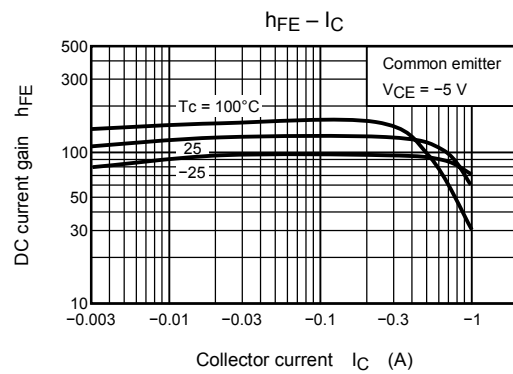
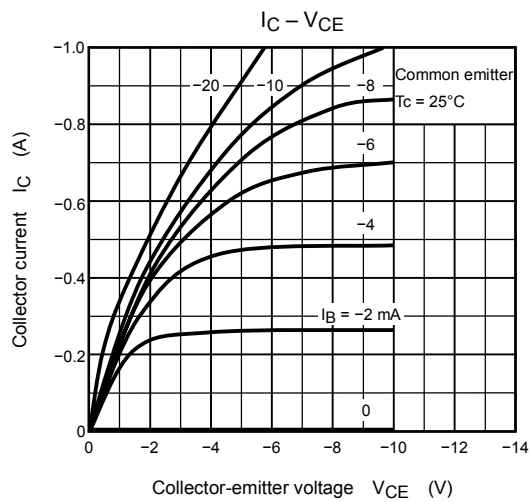
Note: h_{FE} classification O: 70 to 140, Y: 120 to 240

Marking



Explanation of Lot No.





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